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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Nayfeh et al.
Serial No.: 10/829,486
Filed: April 22, 2004
Conf. No.: 6925
For: FAMILY OF DISCRETELY
 SIZED SILICON
 NANOPARTICLES AND
 METHOD FOR PRODUCING
 THE SAME
Art Unit: 1754
Examiner: Unassigned

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October 7, 2004
Date

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INFORMATION DISCLOSURE STATEMENT

Mail Stop AMENDMENT
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

This IDS is submitted under 37 C.F.R. § 1.97(b) within either of the following time periods, whichever occurs last:

- (a) within three months of either the filing date of the national application or the date of entry into the national stage; or
- (b) before the mailing date of first office action on the merits (i.e., not including actions such as restriction requirements).

Applicant(s) submit herewith Form PTO-1449 (Information Disclosure Citation) together with copies of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe may be material to the examination of this application and for which there may be a duty to disclose in accordance with 37 C.F.R. § 1.56. Applicant(s) respectfully submit that the citation of any reference on Form PTO-1449 does not constitute an admission that the reference qualifies as prior art.

It is requested that the information disclosed on the enclosed Form PTO-1449 be made of record in this application.

The Commissioner is hereby authorized to charge any additional fees which may be required to this application under 37 C.F.R. §§ 1.16-1.17, or to credit any overpayment, to Deposit Account No. 07-2069. A duplicate copy of this sheet is enclosed.

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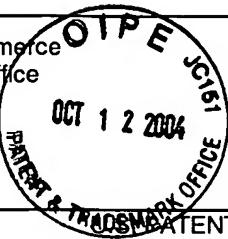
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Respectfully submitted,
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Form PTO-1449 U.S. Department of Commerce
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INFORMATION DISCLOSURE CITATION
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Attorney Docket No.: 1201.70367

Serial No.: 10/826,486

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Filing Date: April 22, 2004

Group: 1754

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Form PTO-1449 U.S. Department of Commerce (Rev. 8-88) Patent and Trademark Office		Attorney Docket No.: 1201.70367	Serial No.: 10/826,486
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